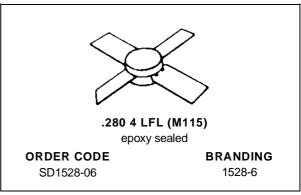


### SD1528-06

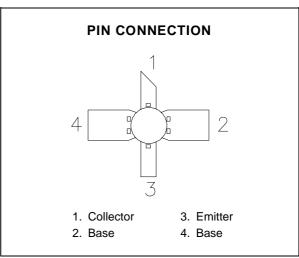
# RF & MICROWAVE TRANSISTORS AVIONICS APPLICATIONS

- DESIGNED FOR HIGH POWER PULSED IFF, DME, TACAN APPLICATIONS
- 20 W (typ.) IFF 1030 1090 MHz
- 15 W (min.) DME 1025 1150 MHz
- 15 W (typ.) TACAN 960 1215 MHz
- REFRACTORY GOLD METALLIZATION
- EMITTER BALLASTED AND LOW THERMAL RESISTANCE FOR RELIABILITY AND RUGGEDNESS
- 20:1 LOAD VSWR CAPABILITY @ SPECIFIED OPERATING CONDITIONS
- INPUT MATCHED, COMMON BASE CONFIGURATION



#### **DESCRIPTION**

The SD1528-06 is a gold metallized epitaxial silicon NPN power transistor. The SD1528-06 is designed for applications requiring high peak power and low duty cycles such as IFF, DME and TACAN. The SD1528-06 is packaged in the .280" input matched stripline package, resulting in improved broadband performance and low thermal resistance.



#### **ABSOLUTE MAXIMUM RATINGS** $(T_{case} = 25^{\circ}C)$

Symbol	Parameter	Value	Unit	
V <sub>CBO</sub>	Collector-Base Voltage	65	V	
V <sub>CES</sub>	Collector-Emitter Voltage	65	V	
V <sub>EBO</sub>	Emitter-Base Voltage	3.5	V	
Ic	Device Current	1.5	А	
Poiss	Power Dissipation	87.5	W	
TJ	Junction Temperature	+200	°C	
T <sub>STG</sub>	Storage Temperature	- 65 to +150	°C	

#### THERMAL DATA

R <sub>TH(j-c)</sub> Junction-Case Thermal Resistance	2.0	°C/W
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November 1992 1/4

#### SD1528-06

#### **ELECTRICAL SPECIFICATIONS** (T<sub>case</sub> = 25°C)

#### **STATIC**

Symbol	Test Conditions	Value			Unit		
		Min.	Тур.	Max.	Unit		
ВУсво	I <sub>C</sub> = 10mA	$I_E = 0mA$		65	_		V
BVces	I <sub>C</sub> = 25mA	$V_{BE} = 0V$		65	_		V
BV <sub>EBO</sub>	I <sub>E</sub> = 1mA	$I_C = 0mA$		3.5	_	_	V
ICES	V <sub>CE</sub> = 50V	$I_E = 0mA$		_	_	2	mA
hFE	V <sub>CE</sub> = 5V	$I_C = .1A$		10	_	200	_

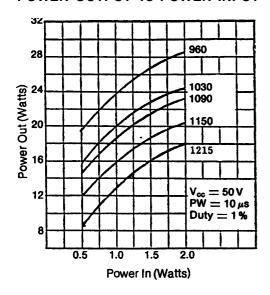
#### **DYNAMIC**

Symbol	Test Conditions		Value			Unit
Symbol	rest Conditions			Тур.	Max.	Oiiit
Pout	f = 1025 — 1150MHz P <sub>IN</sub> = 1.5 W	$V_{CE} = 50 \text{ V}$	15	_	_	W
G <sub>P</sub>	f = 1025 — 1150MHz P <sub>IN</sub> = 1.5 W	$V_{CE} = 50 \text{ V}$	10	_	_	dB
ης	f = 1025 — 1150MHz P <sub>IN</sub> = 1.5 W	$V_{CE} = 50 \text{ V}$	30	_	_	%

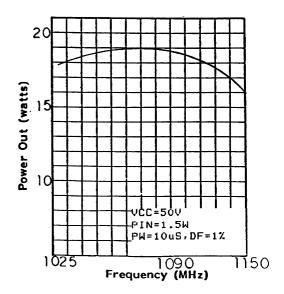
Note: Pulse Width =  $10\mu$ sec, Duty Cycle = 1%

#### **TYPICAL PERFORMANCE**

#### POWER OUTPUT vs POWER INPUT

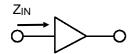


#### **POWER OUTPUT vs FREQUENCY**

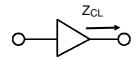


#### **IMPEDANCE DATA**

### TYPICAL INPUT IMPEDANCE

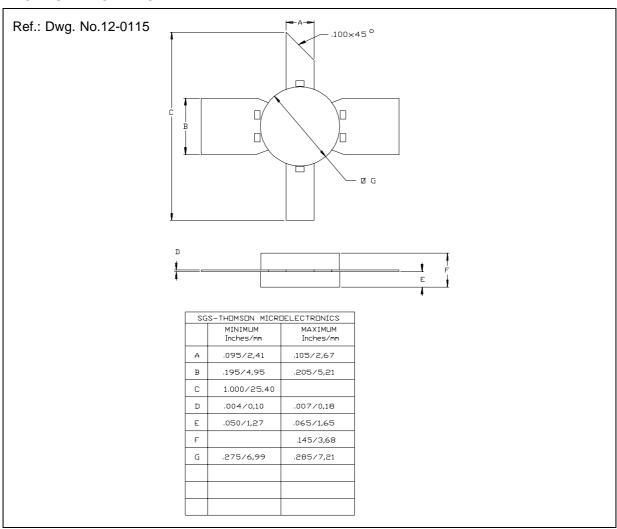


## TYPICAL COLLECTOR LOAD IMPEDANCE



FREQ.	Z <sub>IN</sub> (Ω)	Z <sub>CL</sub> (Ω)		
960 MHz	2.5 + j 12.5	17.0 + j 15.5		
1030 MHz	3.5 + j 12.5	17.0 + j 14.5		
1090 MHz	3.0 + j 13.5	19.5 + j 12.5		
1150 MHz	3.5 + j 14.0	18.0 + j 12.0		
1215 MHz	5.0 + j 17.0	16.0 + j 12.0		

#### **PACKAGE MECHANICAL DATA**



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